

# EUROPEAN PATENT OFFICE

## Patent Abstracts of Japan

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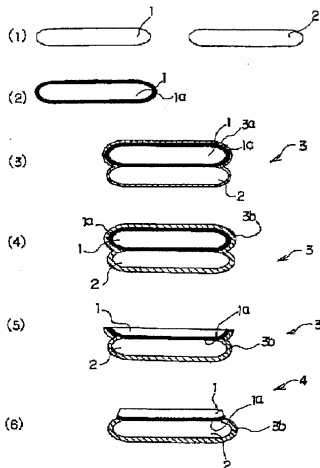
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APPLICANT : SUMITOMO METAL IND LTD;

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TITLE : LAMINATED SEMICONDUCTOR  
SUBSTRATE AND ITS  
MANUFACTURING METHOD



ABSTRACT : PROBLEM TO BE SOLVED: To provide a laminated semiconductor substrate and its manufacturing, method wherein its area comprising an SOI(silicon on insulator) structure is wider, while the manufacturing process is made simple.

SOLUTION: In a laminated semiconductor substrate and its manufacturing method which is formed between a first semiconductor substrate 1 and a second semiconductor substrate 2 with a dielectric layer inbetween, a process in which the first semiconductor substrate and a second semiconductor substrate are pasted together with an oxide film 1a which is to be the dielectric layer in between, and a process where the pasted semiconductor substrate is thermally treated in an oxidation atmosphere and an oxide film 3b is further formed at the periphery part of the dielectric layer present between the first and second semiconductor substrates are provided.

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